

MBRS140LT3

Surface Mount Schottky Power Rectifier

SMB Power Surface Mount Package

This device employs the Schottky Barrier principle in a metal-to-silicon power rectifier. Features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency switching power supplies; free wheeling diodes and polarity protection diodes.

Features

- Compact Package with J-Bend Leads Ideal for Automated Handling
- Highly Stable Oxide Passivated Junction
- Guardring for Over-Voltage Protection
- Low Forward Voltage Drop
- Pb-Free Package is Available

Mechanical Characteristics:

- Case: Molded Epoxy
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 95 mg (Approximately)
- Cathode Polarity Band
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	40	V
Average Rectified Forward Current (At Rated V_R , $T_C = 110^\circ\text{C}$)	I_O	1.0	A
Peak Repetitive Forward Current (At Rated V_R , Square Wave, 100 kHz, $T_C = 110^\circ\text{C}$)	I_{FRM}	2.0	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	40	A
Storage / Operating Case Temperature	T_{stg}, T_C	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature	T_J	-55 to +125	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R , $T_J = 25^\circ\text{C}$)	dv/dt	10,000	V/ μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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SCHOTTKY BARRIER RECTIFIER 1.0 AMPERE – 40 VOLTS



SMB
CASE 403A
PLASTIC

MARKING DIAGRAM



B14L = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MBRS140LT3	SMB	2500/Tape & Reel
MBRS140LT3G	SMB (Pb-Free)	2500/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MBRS140LT3

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Lead (Note 1)	$R_{\theta JL}$	24	$^{\circ}\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	80	$^{\circ}\text{C/W}$

1. Mounted with minimum recommended pad size, PC Board FR4.
2. 1 inch square pad size (1 x 0.5 inch for each lead) on FR4 board.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	$T_J = 25^{\circ}\text{C}$	$T_J = 125^{\circ}\text{C}$	Unit
Maximum Instantaneous Forward Voltage (Note 3) see Figure 2 ($I_F = 1.0\text{ A}$) ($I_F = 2.0\text{ A}$)	V_F	0.5 0.6	0.425 0.58	V
Maximum Instantaneous Reverse Current (Note 3) see Figure 4 ($V_R = 40\text{ V}$) ($V_R = 20\text{ V}$)	I_R	$T_J = 25^{\circ}\text{C}$ 0.4 0.02	$T_J = 100^{\circ}\text{C}$ 10 5.0	mA

3. Pulse Test: Pulse Width $\leq 250\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

MBRS140LT3

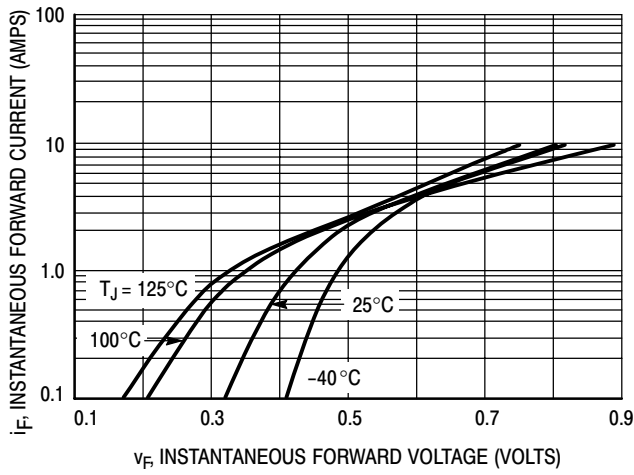


Figure 1. Typical Forward Voltage

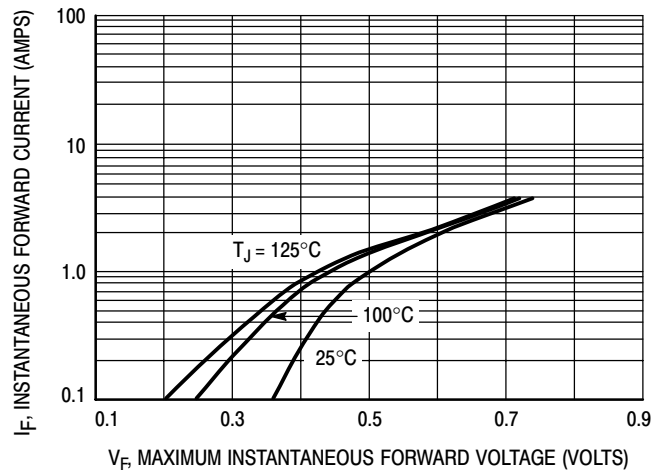


Figure 2. Maximum Forward Voltage

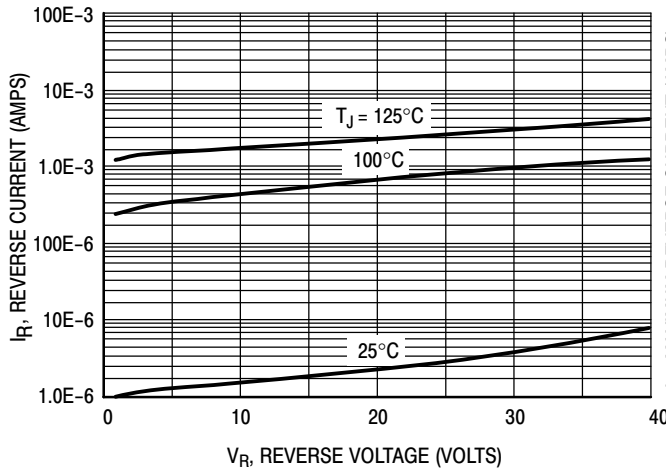


Figure 3. Typical Reverse Current

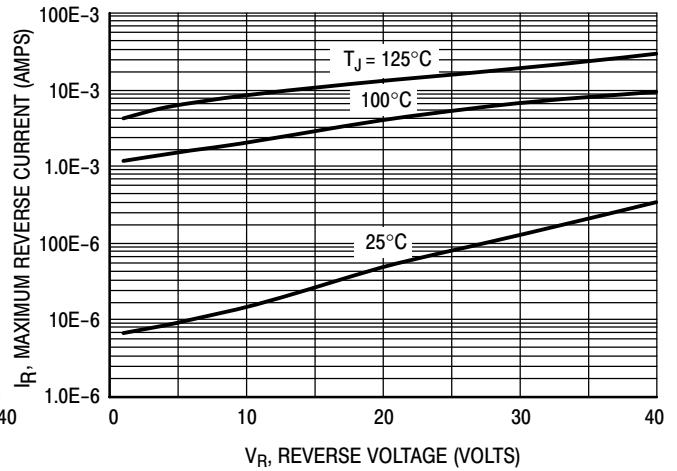


Figure 4. Maximum Reverse Current

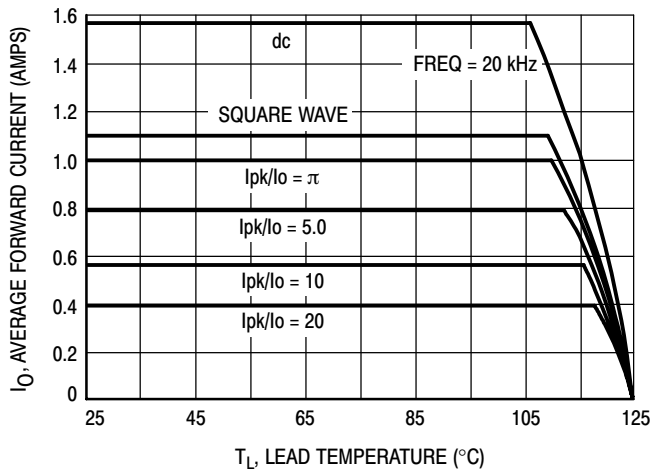


Figure 5. Current Derating

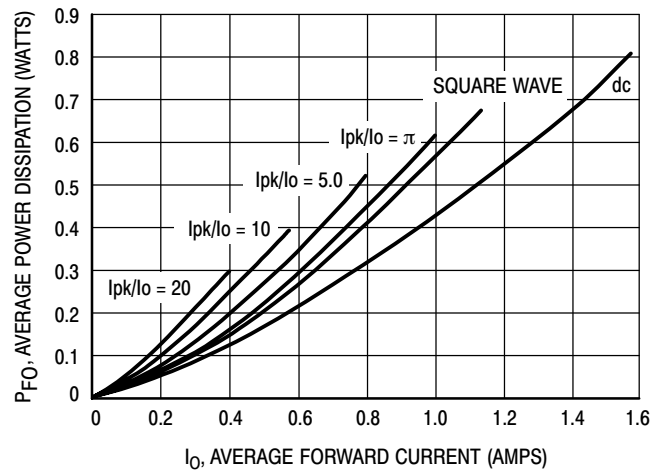


Figure 6. Forward Power Dissipation

MBRS140LT3

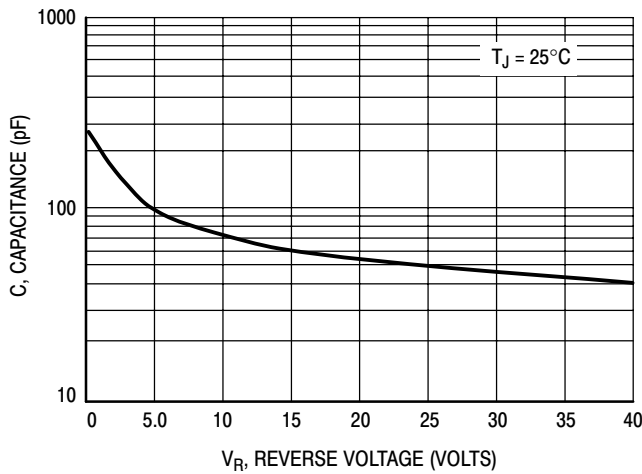


Figure 7. Capacitance

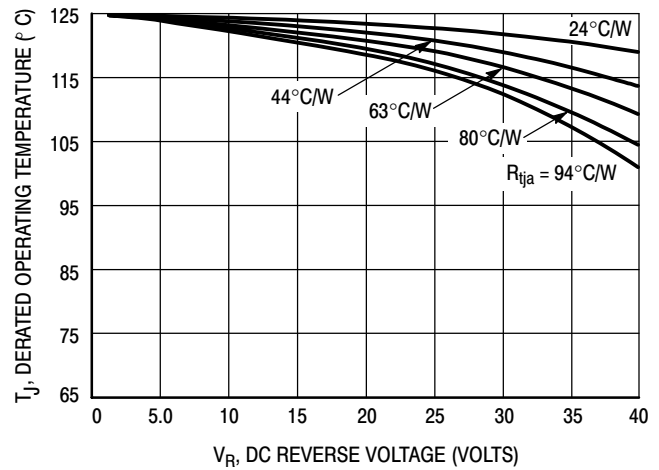


Figure 8. Typical Operating Temperature Derating*

* Reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of T_J therefore must include forward and reverse power effects. The allowable operating T_J may be calculated from the equation:

$$T_J = T_{Jmax} - r(t)(P_f + P_r) \text{ where}$$

$r(t)$ = thermal impedance under given conditions,
 P_f = forward power dissipation, and
 P_r = reverse power dissipation

This graph displays the derated allowable T_J due to reverse bias under DC conditions only and is calculated as $T_J = T_{Jmax} - r(t)P_r$, where $r(t) = R_{\theta JA}$. For other power applications further calculations must be performed.

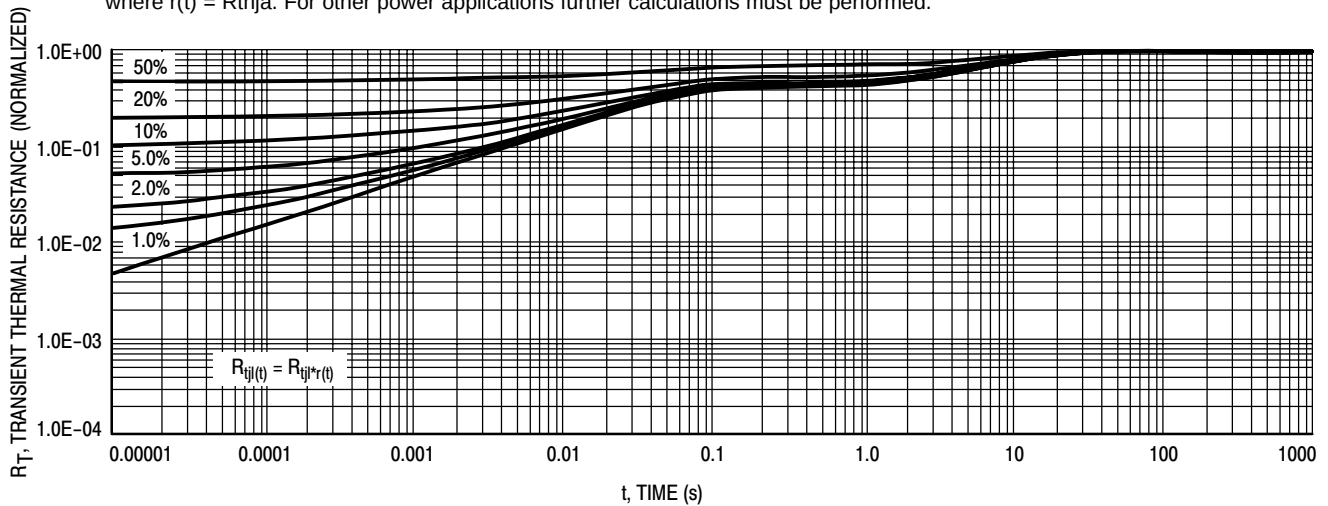


Figure 9. Thermal Response, Junction-to-Lead

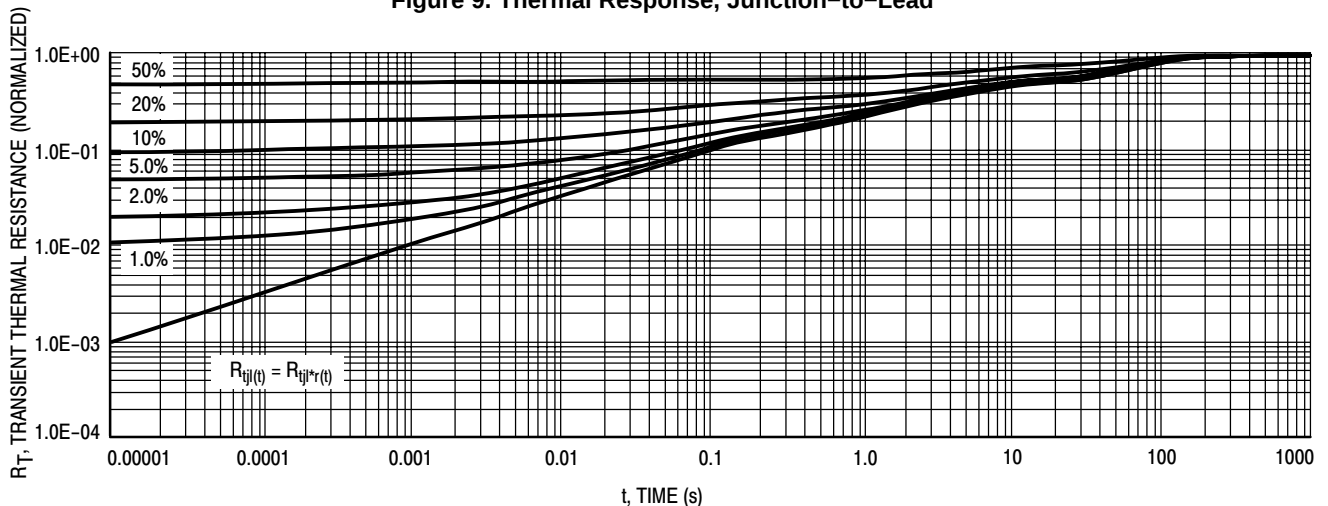


Figure 10. Thermal Response, Junction-to-Ambient

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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ON



SCALE 1:1

Polarity Band

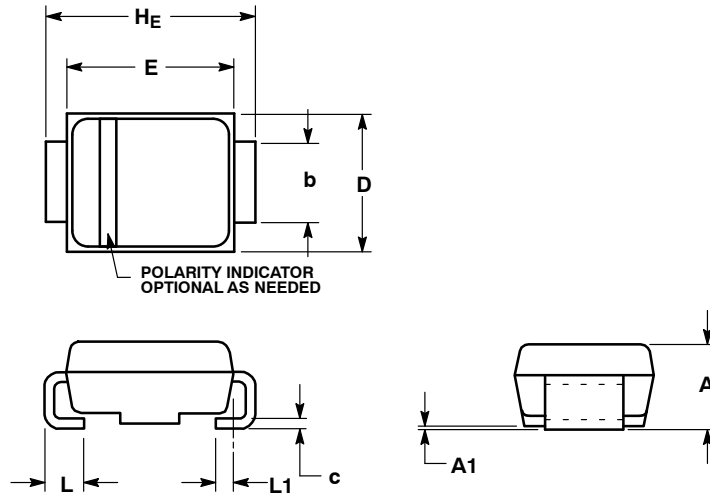


SCALE 1:1

Non-Polarity Band

SMB
CASE 403A-03
ISSUE J

DATE 19 JUL 2012

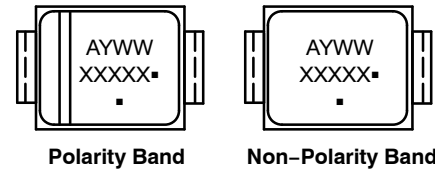


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION b SHALL BE MEASURED WITHIN DIMENSION L1.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.95	2.30	2.47	0.077	0.091	0.097
A1	0.05	0.10	0.20	0.002	0.004	0.008
b	1.96	2.03	2.20	0.077	0.080	0.087
c	0.15	0.23	0.31	0.006	0.009	0.012
D	3.30	3.56	3.95	0.130	0.140	0.156
E	4.06	4.32	4.60	0.160	0.170	0.181
HE	5.21	5.44	5.60	0.205	0.214	0.220
L	0.76	1.02	1.60	0.030	0.040	0.063
L1	0.51 REF			0.020 REF		

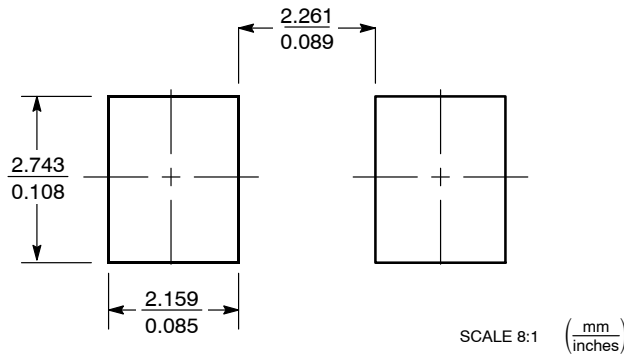
GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package
(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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